

## Quiz - 3

Due Mar 16 at 11:59pm

Points 100

Questions 10

Time Limit None

Allowed Attempts Unlimited

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### Attempt History

	Attempt	Time	Score
KEPT	<a href="#">Attempt 2</a>	2 minutes	100 out of 100
LATEST	<a href="#">Attempt 2</a>	2 minutes	100 out of 100
	<a href="#">Attempt 1</a>	35 minutes	40 out of 100

❗ Correct answers are hidden.

Score for this attempt: **100** out of 100

Submitted Mar 15 at 9:43pm

This attempt took 2 minutes.

#### Question 1

10 / 10 pts

1. By definition, the minimum time from input to rising output crossing  $V_{DD}/2$  is:

- ☐ Rise Time - ( $t_r$ )
- ☐ Setup - time
- ☒ Rising Contamination delay ( $t_{cdr}$ )
- ☐ Rising Propagation Delay ( $t_{pdr}$ )

#### Question 2

10 / 10 pts

In RC Delay Model, which of the following substitutions is valid?

- ☐ NMOS transistor with a width of  $k$  times the unit transistor has a resistance of  $2R/k$
- ☐ PMOS transistor with a width of  $k$  times the unit transistor has a resistance of  $R/k$
- ☐ NMOS transistor with a width of  $k$  times the unit transistor has a cap of  $2kC$  on the gate
- ☒ PMOS transistor with a width of  $k$  times the unit transistor has a cap of  $kC$  on the gate

**Question 3****10 / 10 pts**

The falling delay is affected by the resistance in the \_\_\_\_\_ network?

☒ PDN☐ PUN**Question 4****10 / 10 pts**

The rising delay is affected by the resistance in the \_\_\_\_\_ network?

☒ PUN☐ PDN**Question 5****10 / 10 pts**

A 2-input NAND gate is designed to achieve the effective Resistance of a unit inverter for PUN and PDN. It has a fan-out of 1.

What is the  $K_p$  value for the NAND gate above?

☐  $K_p = 1$ ☐  $K_p = 8$ ☒  $K_p = 2$ ☐  $K_p = 4$ **Question 6****10 / 10 pts**

A 2-input NAND gate is designed to achieve the effective Resistance of a unit inverter for PUN and PDN. It has a fan-out of 1.

What is the  $K_n$  value for the NAND gate above?

- ☒  $K_n = 2$
- ☐  $K_n = 8$
- ☐  $K_n = 4$
- ☐  $K_n = 1$

### Question 7

10 / 10 pts

A 2-input NAND gate is designed to achieve the effective Resistance of a unit inverter for PUN and PDN. It has a fan-out of 1.

For the NAND gate above, what is the value of the parasitic delay,  $t_{pdr}$ , worst case (load-free component)?

- ☒  $6RC$
- ☐  $12RC$
- ☐  $5RC$
- ☐  $8RC$

### Question 8

10 / 10 pts

A 2-input NAND gate is designed to achieve the effective Resistance of a unit inverter for PUN and PDN. It has a fan-out of 1.

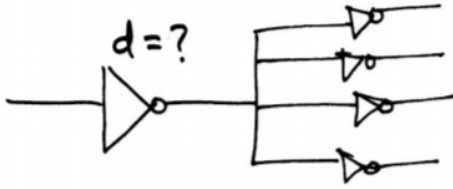
For the NAND gate above, what is the value of the delay from the load (parasitic-free component)?

- ☐  $5RC$
- ☐  $12RC$
- ☐  $6RC$
- ☒  $4RC$

**Question 9****10 / 10 pts**

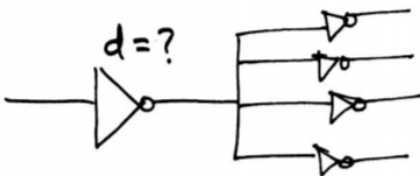
For the figure shown below, what is the parasitic delay in terms of  $T$ ?

( $T$  is defined as the delay of a parasitic-free fanout-of-1 inverter)

☐  $2T$ ☐  $4T$ ☒  $1T$ ☐  $3T$ **Question 10****10 / 10 pts**

For the figure shown below, what is the load (fanout) delay in terms of  $T$ ?

( $T$  is defined as the delay of a parasitic-free fanout-of-1 inverter)

☐  $1T$ ☒  $4T$ ☐  $3T$ ☐  $2T$ Quiz Score: **100** out of 100